Thyristors BT151X series

GENERAL DESCRIPTION

Glass passivated thyristors in a full pack, plastic envelope, intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

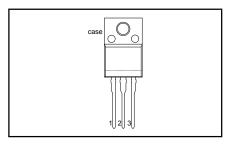
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V _{DRM} ,	BT151X- Repetitive peak off-state voltages	500 500	650 650	800 800	V
V _{RRM} I _{T(AV)} I _{T(RMS)} I _{TSM}	Average on-state current RMS on-state current Non-repetitive peak on-state current	5.7 9 100	5.7 9 100	5.7 9 100	A A A

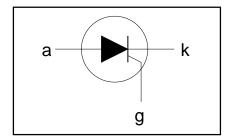
PINNING - SOT186A

PIN	DESCRIPTION
1	cathode
2	anode
3	gate
case	isolated

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
V_{DRM} , V_{RRM}	Repetitive peak off-state voltages		-	-500 500 ¹	-650 650 ¹	-800 800	V
I _{T(AV)} I _{T(RMS)} I _{TSM}	Average on-state current RMS on-state current Non-repetitive peak on-state current	half sine wave; $T_{hs} \le 87 ^{\circ}\text{C}$ all conduction angles half sine wave; $T_j = 25 ^{\circ}\text{C}$ prior to surge	-		5.7 9		A A
12.		t = 10 ms t = 8.3 ms	- -		100 110		A A
l²t dl _⊤ /dt	I ² t for fusing Repetitive rate of rise of on-state current after triggering	t = 10 ms $I_{TM} = 20 \text{ A}; I_G = 50 \text{ mA};$ $dI_G/dt = 50 \text{ mA/}\mu\text{s}$	-		50 50		A²s A/μs
I _{GM} V _{GM} V _{RGM}	Peak gate current Peak gate voltage Peak reverse gate voltage		- - -		2 5 5 5		A V V W
P _{GM} P _{G(AV)} T _{stg} T _j	Peak gate power Average gate power Storage temperature Operating junction temperature	over any 20 ms period	- -40 -		0.5 150 125		ů Ç Ç

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/ μ s.

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ISOLATION LIMITING VALUE & CHARACTERISTIC

 T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	R.M.S. isolation voltage from all three terminals to external heatsink	f = 50-60 Hz; sinusoidal waveform; R.H. ≤ 65%; clean and dustfree	. 1		2500	V
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	1	10	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th j-hs}$ $R_{th j-a}$	Thermal resistance junction to heatsink Thermal resistance junction to ambient	with heatsink compound without heatsink compound in free air	1 1 1	- - 55	4.5 6.5 -	K/W K/W K/W

STATIC CHARACTERISTICS

 $T_j = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-	2	15	mΑ
I _L	Latching current	$V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$	-	10	40	mΑ
I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	7	20	mΑ
Ϋ́Τ	On-state voltage	$I_{T} = 23 \text{ A}$	-	1.4	1.75	V
V _{GT}	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$	-	0.6	1.5	V
		$V_{\rm D} = V_{\rm DRM(max)}$; $I_{\rm T} = 0.1 \text{ A}$; $T_{\rm i} = 125 ^{\circ}\text{C}$	0.25	0.4	-	V
I_D, I_R	Off-state leakage current	$V_D = V_{DRM(max)}^{Station}$; $V_R = V_{RRM(max)}$; $T_j = 125 ^{\circ}C$	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of off-state voltage	V _{DM} = 67% V _{DRM(max)} ; T _j = 125 °C; exponential waveform Gate open circuit	50	130	_	V/us
		$R_{GK} = 100 \Omega$	200	1000	_	V/μS V/μS
t _{gt}	Gate controlled turn-on time	$I_{TM} = 40 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$		2	-	μs
t _q	Circuit commutated turn-off time	$ \begin{array}{l} V_{D} = 67\% \ V_{DRM(max)}; \ T_{j} = 125 \ ^{\circ}C; \\ I_{TM} = 20 \ A; \ V_{R} = 25 \ V; \ dI_{TM}/dt = 30 \ A/\mu s; \\ dV_{D}/dt = 50 \ V/\mu s; \ R_{GK} = 100 \ \Omega \end{array} $	-	70	-	μs

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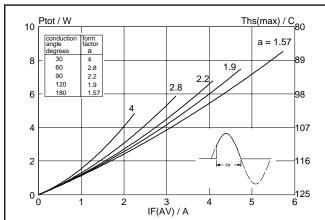


Fig.1. Maximum on-state dissipation, P_{tot} , versus average on-state current, $I_{T(AV)}$, where $a = form\ factor = I_{T(RMS)}/I_{T(AV)}$.

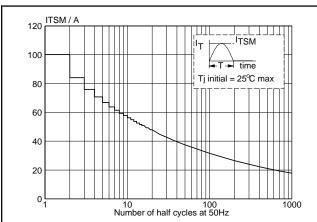


Fig.4. Maximum permissible non-repetitive peak on-state current I_{TSM}, versus number of cycles, for sinusoidal currents, f = 50 Hz.

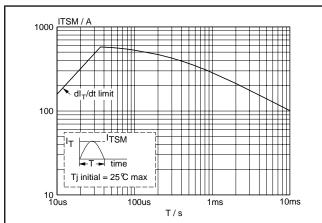


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 10$ ms.

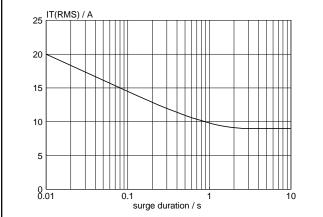


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{hs} \le 87$ °C.

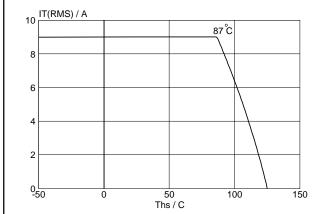


Fig.3. Maximum permissible rms current $I_{T(RMS)}$, versus heatsink temperature T_{hs} .

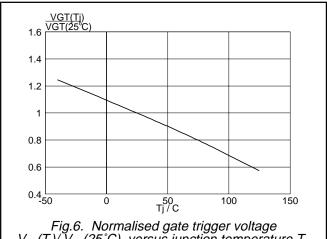
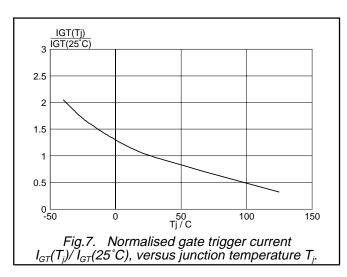
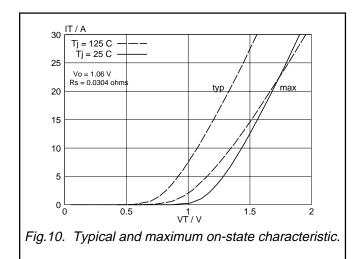
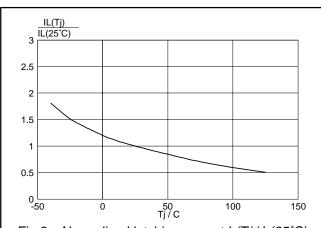


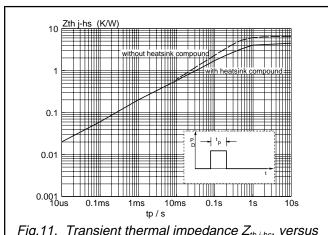
Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$, versus junction temperature $T_{j^{\circ}}$

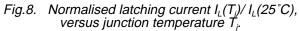
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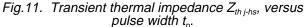


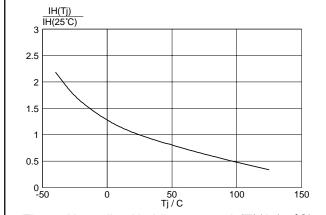












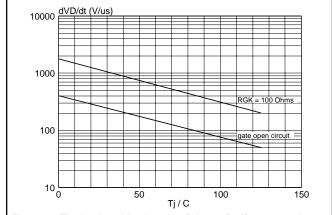
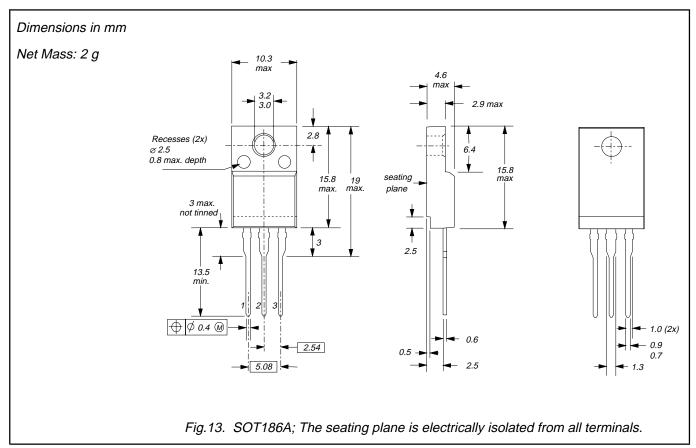


Fig.9. Normalised holding current $I_H(T_i)/I_H(25^{\circ}C)$, versus junction temperature T_j .

Fig.12. Typical, critical rate of rise of off-state voltage, dV_D/dt versus junction temperature T_i.

BT151X series **Thyristors**

MECHANICAL DATA



- Notes
 1. Refer to mounting instructions for F-pack envelopes.
 2. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status						
This data sheet contains target or goal specifications for product development.						
This data sheet contains preliminary data; supplementary data may be published later.						
This data sheet contains final product specifications.						
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Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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